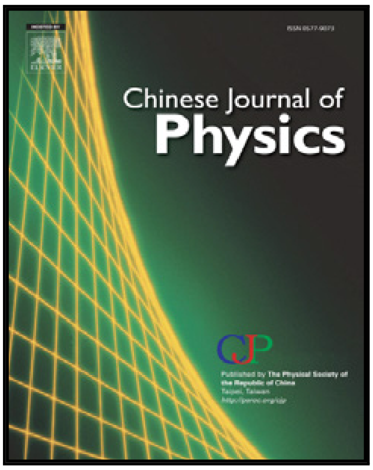

Formation of $Ge_{35}In_8S_{57}$ amorphous films for optical applications

M. Rashad , A.A.A. Darwish , Said A. Farha Al-Said , A.A. Hendi , M.M. Hafiz

PII: S0577-9073(17)30721-9
DOI: 10.1016/j.cjph.2017.12.021
Reference: CJPH 423

To appear in: *Chinese Journal of Physics*

Received date: 12 June 2017
Revised date: 23 December 2017
Accepted date: 26 December 2017

Please cite this article as: M. Rashad , A.A.A. Darwish , Said A. Farha Al-Said , A.A. Hendi , M.M. Hafiz , Formation of $Ge_{35}In_8S_{57}$ amorphous films for optical applications, *Chinese Journal of Physics* (2017), doi: 10.1016/j.cjph.2017.12.021

Highlights

- Study the structure, optical and electrical properties of $Ge_{35}In_8S_{57}$ with different film thickness.
- Structural investigations of $Ge_{35}In_8S_{57}$ system have been studied.
- The linear and nonlinear studies have been studied for these films.
- The third order nonlinear optical susceptibility of the present system is calculated.